1. Scope :

This specification applies to PIN silicon photodiode chips,
Device No. PD-3062

2. Structure :

2-1. Planar type : PIN diode.
2-2. Electrodes :
Top side (Anode) : Aluminum alloy .
Top side (Cathode) : Aluminum alloy .

3. Size :

3-1. Chip size : 63 mils x 63 mils (1.6 mm x 1.6 mm).
3-2. Chip thickness : 12 ± 1.5mils (0.305 ± 0.038 mm).
3-3. Active area : 53 mils x 53 mils (1.346 mm x 1.346 mm).
3-4. Bonding pad (Anode) : 6 mils x 6 mils (0.153 mm x 0.153 mm)
(Cathode) : 6 mils x 6 mils (0.153 mm x 0.153 mm)
3-5. Pattern drawing : Refer to the attached drawing.

4. Electro-optical characteristics (Ta = 25℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
※Reverse dark Current	I_D	V_R=10V Ee=0mW/cm^2			10	nA
※Reverse breakdown voltage	$V_{(BR)R}$	I_R=100uA Ee=0mW/cm^2	60			V
Open circuit Voltage	Voc	T=2856K Ee=5mW/cm^2		410		mV
Short circuit Current	Isc	T=2856K Ee=5mW/cm^2		21		μA
Reverse light Current	I_L	V_R =5V T=2856K Ee=5mW/cm^2		21		μA
Total Capacitance	Ct	V_R =5V Ee=0mW/cm^2 f=1MHz		5		pF
Turn-on/ Turn-off Time	Ton/toff	V_R=2V R_L=200Ω λ=905nm		250/550		ns

※Based on 100% probing